Si2300DS

30V/3.6A N-Channel MOSFET

Features

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching

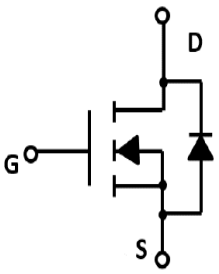
Application

- Battery protection
- Load switch
- Power management

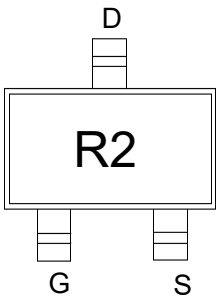
Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	68mΩ@4.5V	3.6A
	85mΩ@2.5V	

SOT-23 top view



Schematic diagram



R2: Device code

Marking and pin assignment

Pb-Free RoHS Halogen-Free

Absolute Maximum Ratings (TA=25℃unless otherwise noted)				
Symbol	**Parameter**		**Rating**	**Unit**
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		30	V
V_{GS}	Gate-Source Voltage		±12	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C	1.4	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	15	A
I_D	Continuous Drain Current	Tc=25°C	3.6	A
P_D	Maximum Power Dissipation	Tc=25°C	1.7	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		104	°C/W

Ordering Information (Example)						
Type	**Package**	**Marking**	**Minimum Package(pcs)**	**Inner Box Quantity(pcs)**	**Outer Carton Quantity(pcs)**	**Delivery Mode**
Si2300DS	SOT-23	R2	3,000	45,000	180,000	7"reel

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Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	**Parameter**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V，I_D=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V，V_{GS}=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±12V，V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}，I_D=250μA	0.6	--	1.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=4.5V， I_D=2.9A	--	55	68	mΩ
		V_{GS}=2.5V，I_D=2.6A	--	70	85	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=15V，V_{GS}=0V， f=1MHz	--	320	--	pF
C_{OSS}	Output Capacitance		--	45	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	19	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=15V，I_D=3.1A，V_{GS}=4.5V	--	3	--	nC
Q_{gs}	Gate Source Charge		--	0.8	--	nC
Q_{gd}	Gate Drain Charge		--	0.5	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V，I_D=2.5A，V_{GS}=4.5V，R_G=1Ω，R_L=6Ω	--	10	--	nS
t_r	Turn-on Rise Time		--	15	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	20	--	nS
t_f	Turn-Off Fall Time		--	11	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃，Is=2.5A	--	0.8	1.2	V

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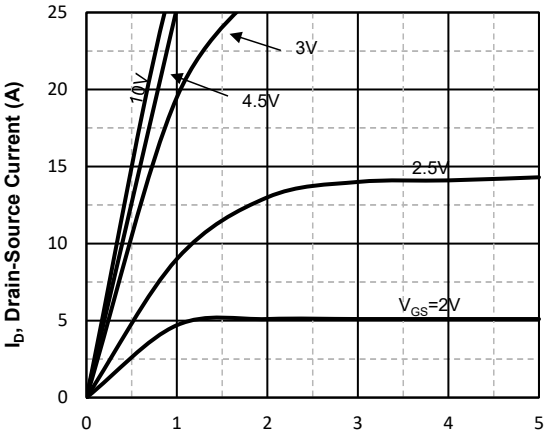
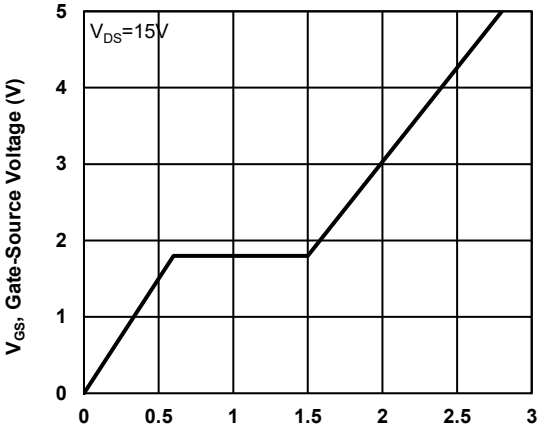
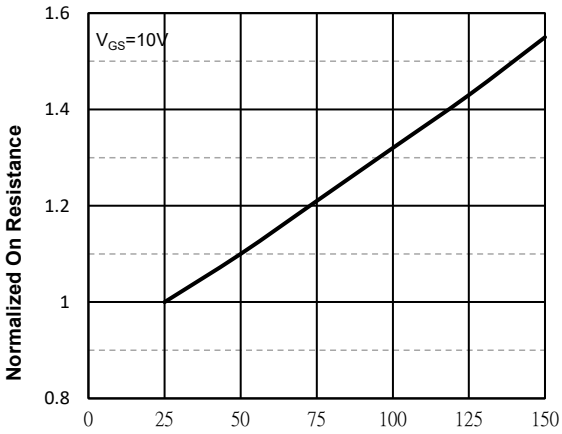
Typical Operating Characteristics



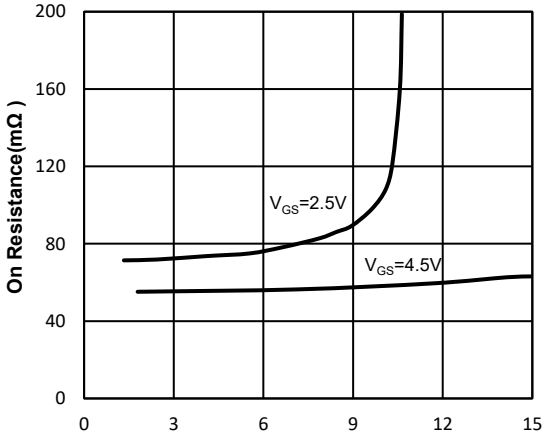
V_{DS}, Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



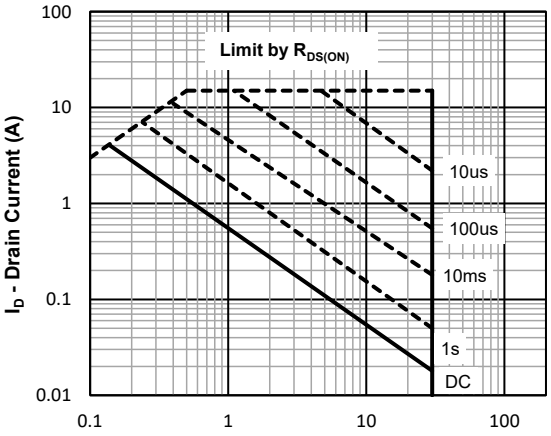
Qg -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs.Gate-Source Voltage



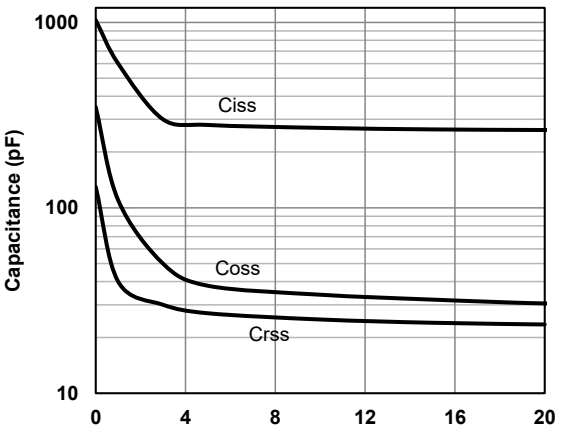
Tj - Junction Temperature (°C)
Fig3. Normalized On-Resistance Vs. Temperature



I_D, Drain-Source Current (A)
Fig4. On-Resistance Vs. Drain-Source



V_{DS}, Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



V_{DS} , Drain-Source Voltage (V)
Fig6 Typical Capacitance Vs.Drain-Source Voltage

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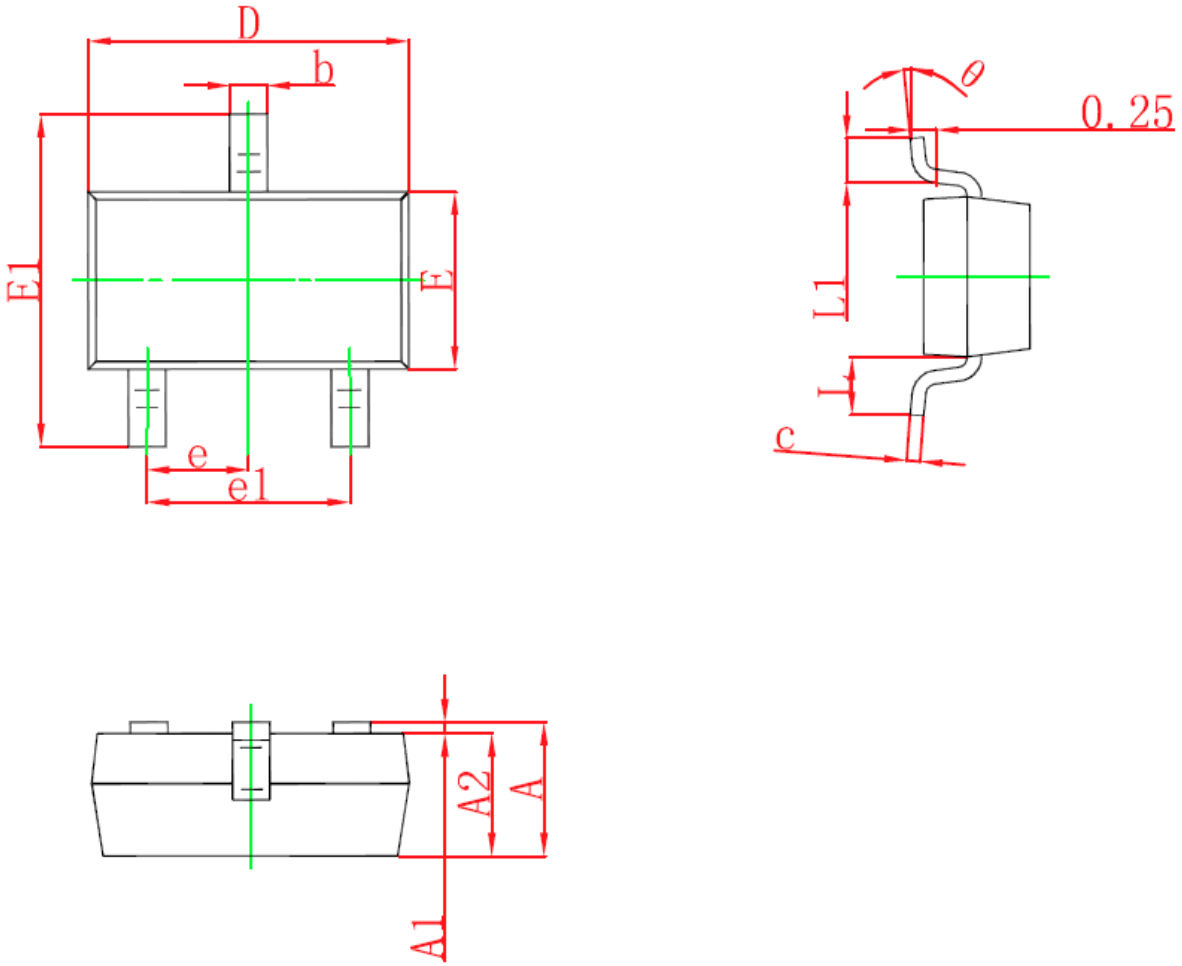
SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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